



## Features

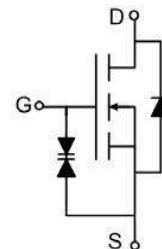
- N-Channel
- Advanced Trench Technology
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead free product is acquired
- ESD Protected: 2KV

$V_{DS}$	60	V
$R_{DS(on),TYP}$ @ $V_{GS}=10\text{ V}$	1.7	$\Omega$
$R_{DS(on),TYP}$ @ $V_{GS}=4.5\text{ V}$	2.0	$\Omega$
$I_D$	0.2	A

SOT-523



Part ID	Package Type	Marking	Packing
ZT72FN06	SOT-523	72F	3000pcs/Reel



## Absolute Maximum Ratings $T_A=25^\circ\text{C}$ , unless otherwise specified

Symbol	Parameter	Rating	Unit	
<b>Common Ratings (<math>T_c=25^\circ\text{C}</math> Unless Otherwise Noted)</b>				
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	60	V	
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
$I_{DM}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	$T_c=25^\circ\text{C}$	1.2	A
<b>Mounted on Large Heat Sink</b>				
$I_D$	Drain Current-Continuous	$T_c=25^\circ\text{C}$	0.2	A
		$T_c=100^\circ\text{C}$	0.19	A
$P_D$	Maximum Power Dissipation	0.35	W	
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	357	$^\circ\text{C}/\text{W}$	



**Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ <math>T_J=25^\circ\text{C}</math> (unless otherwise stated)</b>						
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	60	--	--	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}, V_{GS}=0\text{V}$	--	--	1	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	1.5	2.5	V
$R_{DS(\text{on})}$	Drain-Source On-State Resistance	$V_{GS}=10\text{V}, I_D=0.3\text{A}$	--	1.7	2.2	$\Omega$
$R_{DS(\text{on})}$	Drain-Source On-State Resistance	$V_{GS}=4.5\text{V}, I_D=0.2\text{A}$	--	2.0	2.9	$\Omega$
<b>Dynamic Electrical Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
C <sub>iss</sub>	Input Capacitance	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$	--	28	--	pF
C <sub>oss</sub>	OutputCapacitance		--	11	--	pF
C <sub>rss</sub>	ReverseTransferCapacitance		--	4	--	pF
Q <sub>g</sub>	Total Gate Charge	$V_{DS}=10\text{V}, I_D=0.3\text{A}, V_{GS}=4.5\text{V}$	--	1.7	--	nC
Q <sub>gs</sub>	Gate-SourceCharge		--	0.3	--	nC
Q <sub>gd</sub>	Gate-DrainCharge		--	0.6	--	nC
<b>Switching Characteristics</b>						
T <sub>d(on)</sub>	Turn-on Delay Time	$V_{DD}=10\text{V}, I_D = 0.2\text{A}, R_G=10\Omega, V_{GS}=10\text{V}$	--	2	--	ns
T <sub>r</sub>	Turn-on Rise Time		--	15	--	ns
T <sub>d(off)</sub>	Turn-Off Delay Time		--	7	--	ns
T <sub>f</sub>	Turn-Off Fall Time		--	20	--	ns
<b>Source- Drain Diode Characteristics@ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
I <sub>SD</sub>	Source-Drain Current (Body Diode)		--	--	0.2	A
V <sub>SD</sub>	Forward on voltage	$I_S=0.3\text{A}, V_{GS}=0\text{V}$	--	--	1.2	V

**Notes:**

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$ , Duty Cycle $\leq 2\%$

## Typical Performance Characteristics

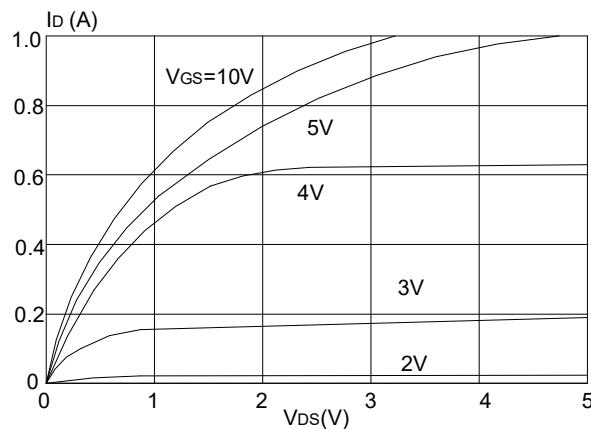


Figure 1: Output Characteristics

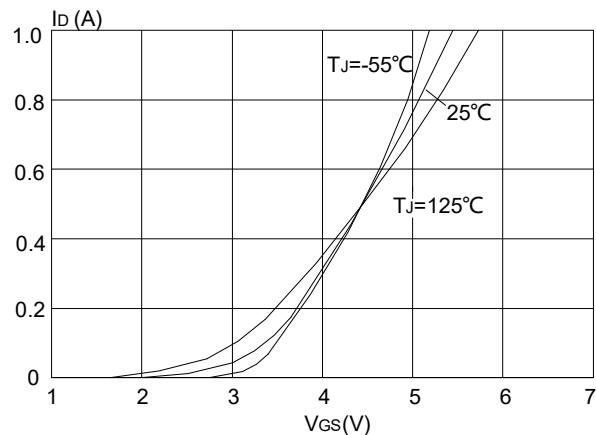


Figure 4: Typical Transfer Characteristics

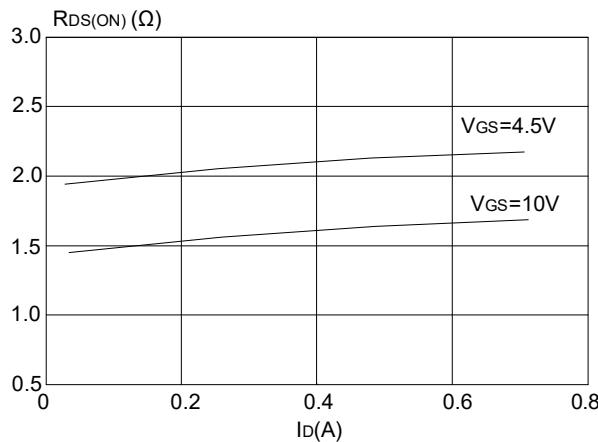


Figure 2: On-resistance vs. Drain Current

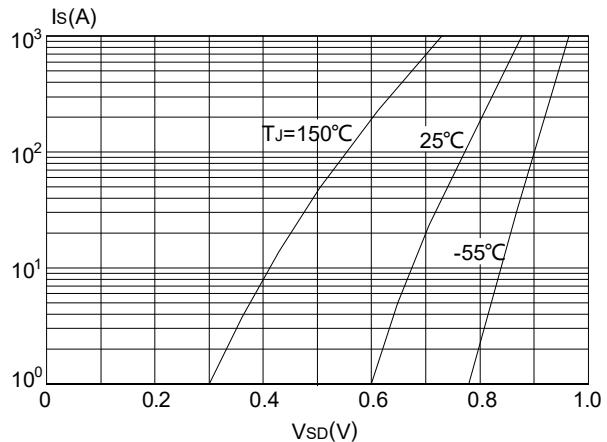


Figure 5: Body Diode Characteristics

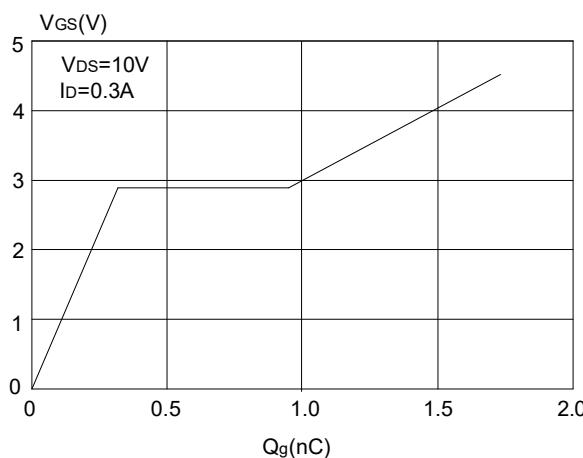


Figure 3: Gate Charge Characteristics

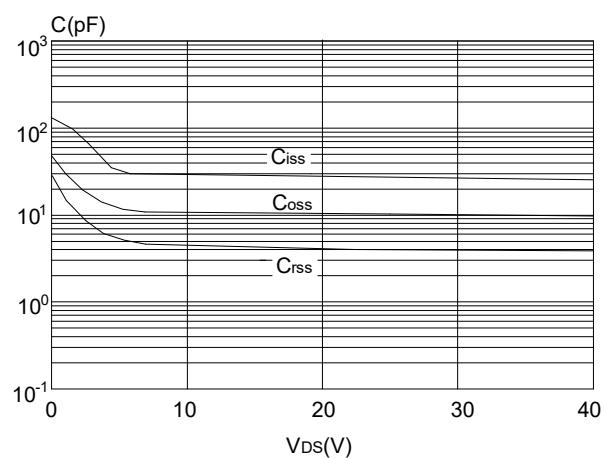
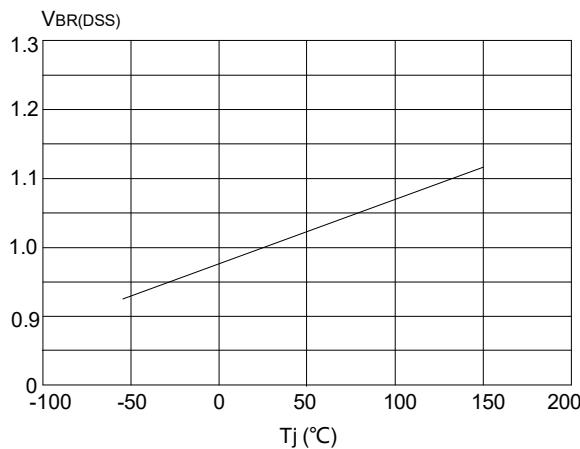
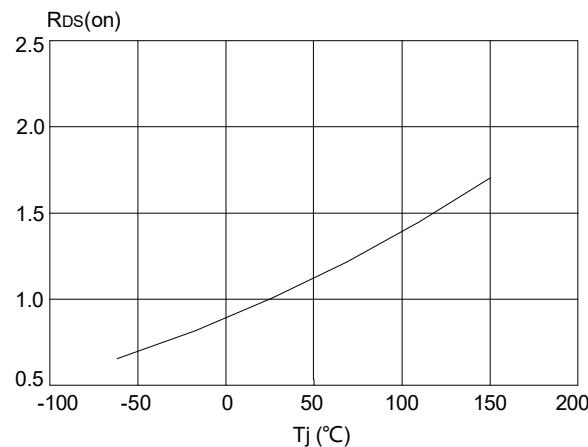


Figure 6: Capacitance Characteristics

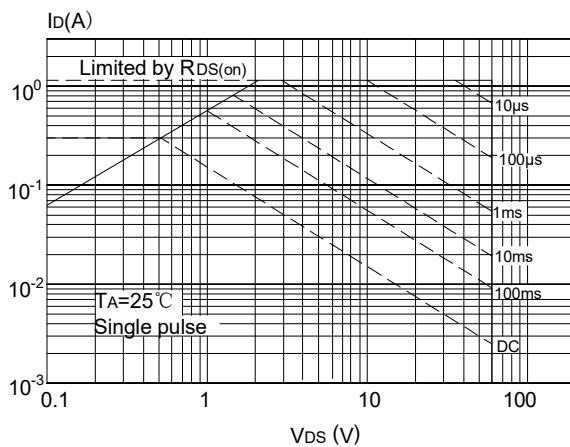
## Typical Performance Characteristics



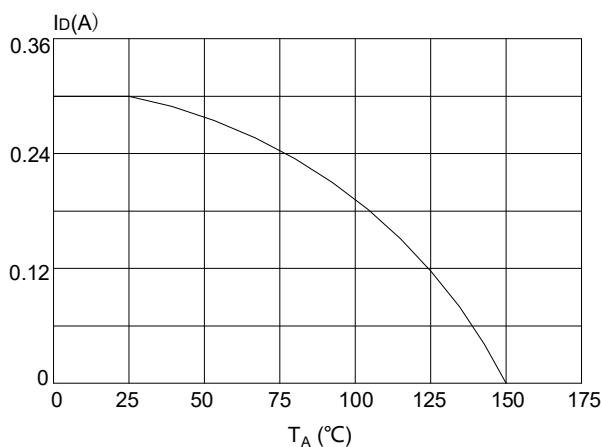
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



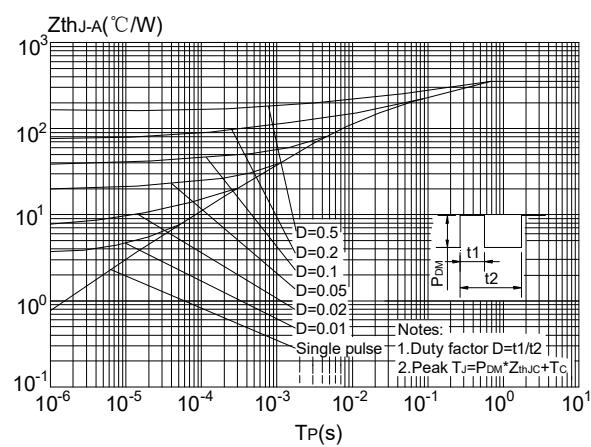
**Figure 9:** Normalized on Resistance vs. Junction Temperature



**Figure 8:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

## Test Circuit

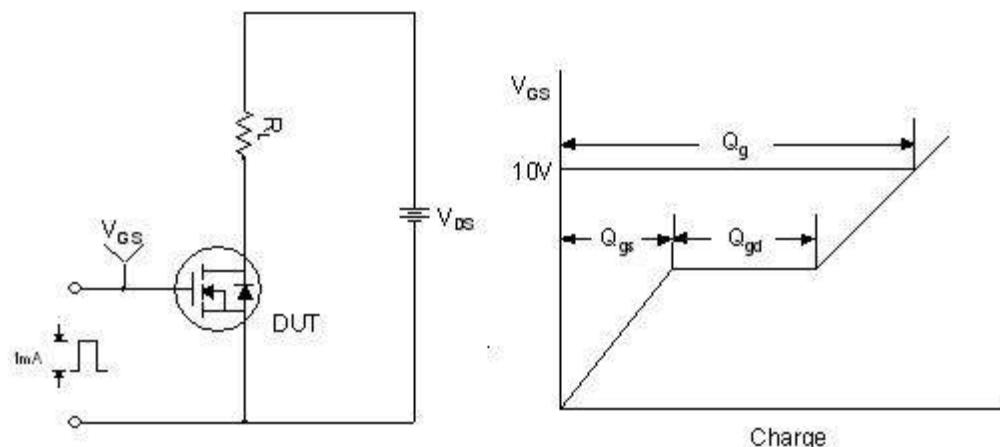


Figure 1. Gate Charge Test Circuit & Waveform

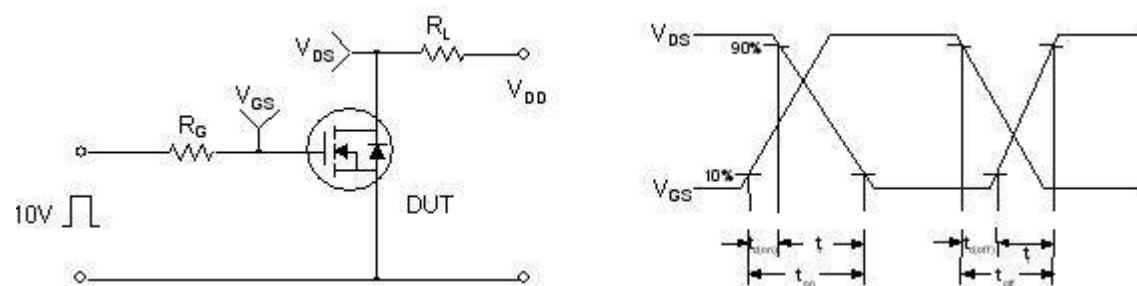


Figure 2. Resistive Switching Test Circuit & Waveforms

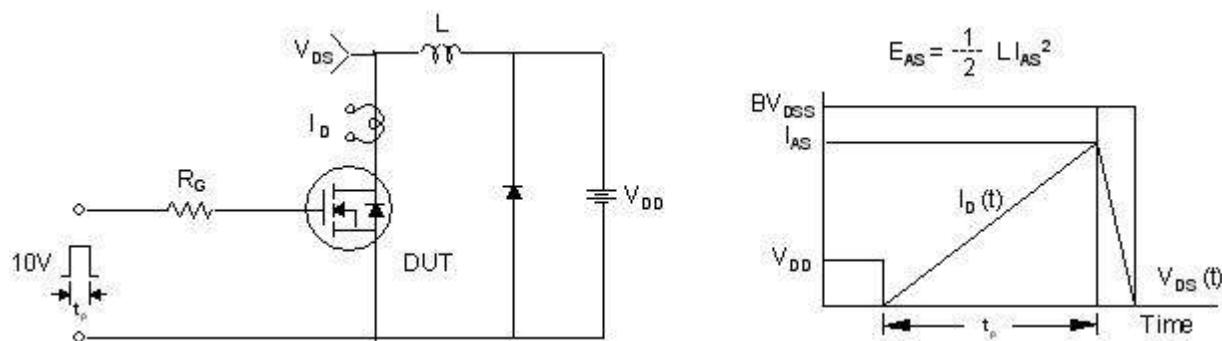
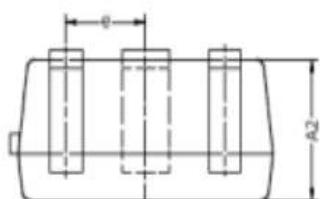
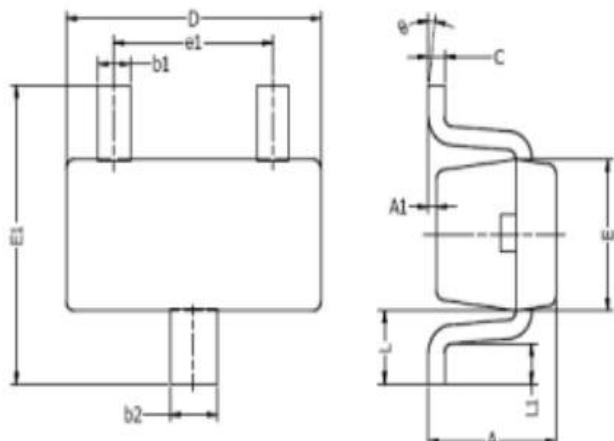


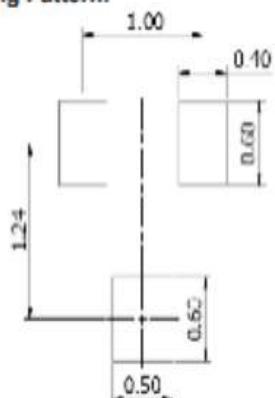
Figure 3. Unclamped Inductive Switching Test Circuit & Waveforms



## SOT-523 Package Information



Typical Soldering Pattern:



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
$\theta$	0°	8°	0°	8°

## Customer Service

### Sales and Service:

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